

# BCR16RM-12LB

## Triac

Medium Power Use

REJ03G1714-0100

Rev.1.00

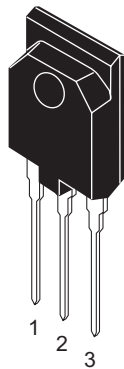
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### Features

- $I_{T(RMS)}$  : 16 A
- $V_{DRM}$  : 600 V
- $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGTHI}$  : 30 mA
- $V_{ISO}$  : 2000 V
- The product guaranteed maximum junction temperature of 150°C
- Insulated Type
- Planar Passivation Type

### Outline

RENESAS Package code: PRSS0003ZA-A  
(Package name: TO-3PFM)



1. T<sub>1</sub> Terminal
2. T<sub>2</sub> Terminal
3. Gate Terminal

### Applications

Contactless AC switch, electric heater control, light dimmer, on/off and speed control of small induction motor, on/off control of copier lamp

### Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_T$ (RMS)	16	A	Commercial frequency, sine full wave 360° conduction, $T_c = 117^\circ\text{C}$
Surge on-state current	$I_{TSM}$	160	A	50 Hz sinewave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusing	$I^2t$	128	$\text{A}^2\text{s}$	Value corresponding to 1 cycle of half wave 50 Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	$I_{GM}$	2	A	
Junction temperature	$T_j$	- 40 to +150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	- 40 to +150	$^\circ\text{C}$	
Mass	—	5.2	g	Typical value
Isolation voltage	$V_{iso}$	2000	V	$T_a = 25^\circ\text{C}$ , AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

## Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	$I_{DRM}$	—	—	2.0	mA	$T_j = 150^\circ\text{C}$ , $V_{DRM}$ applied
On-state voltage	$V_{TM}$	—	—	1.5	V	$T_c = 25^\circ\text{C}$ , $I_{TM} = 25\text{ A}$ , Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	—	—	1.5	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$V_{RGTI}$	—	—	1.5	
	III	$V_{RGTIII}$	—	—	1.5	
Gate trigger current <sup>Note2</sup>	I	$I_{FGTI}$	—	—	30	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$I_{RGTI}$	—	—	30	
	III	$I_{RGTIII}$	—	—	30	
Gate non-trigger voltage	$V_{GD}$	0.2/0.1	—	—	V	$T_j = 125^\circ\text{C}/150^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	1.8	$^\circ\text{C}/\text{W}$	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>	$(dv/dt)_c$	10/1	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}/150^\circ\text{C}$

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $0.5^\circ\text{C}/\text{W}$ .

4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}/150^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -8.0\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	